Features

- Trench LV MOSFET Technology
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

P-Channel MOSFET

Maximum Ratings

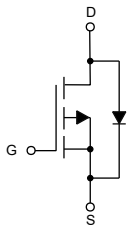
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 504°C/W Junction to Ambient (Note2)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-0.2	A
	T_A=100°C		-0.13	
Pulsed Drain Current (Note3)		I_{DM}	-0.8	A
Total Power Dissipation (Note4)		P_D	0.25	W

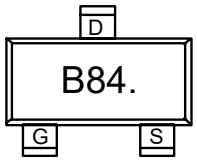
Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction-ambient thermal resistance.

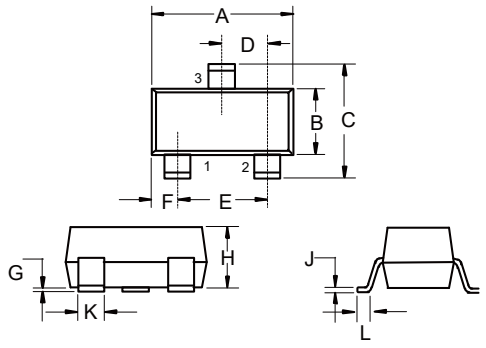
Internal Structure and Marking Code



1. GATE
2. SOURCE
3. DRAIN

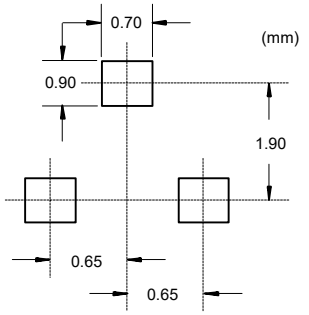


SOT-323



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.083	0.096	2.10	2.45	
D	0.026		0.65		TYP.
E	0.047	0.055	1.20	1.40	
F	0.012	0.016	0.30	0.40	
G	0.000	0.004	0.00	0.10	
H	0.035	0.044	0.90	1.10	
J	0.002	0.010	0.05	0.25	
K	0.006	0.016	0.15	0.40	
L	0.010	0.018	0.26	0.46	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-0.9	-1.4	-2.0	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-0.15A		3.0	3.9	Ω
		V_{GS}=-4.5V, I_D=-0.15A		3.5	4.6	
Gate Resistance	R_g	f=1 MHz, Open Drain		48		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-0.2	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-0.17A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-0.19A,di/dt=100A/μs		20		ns
Reverse Recovery Charge	Q_{rr}			10		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-30V,V_{GS}=0V,f=1MHz		23		pF
Output Capacitance	C_{oss}			3.4		
Reverse Transfer Capacitance	C_{rss}			1.7		
Total Gate Charge	Q_g	V_{DS}=-30V,V_{GS}=-10V,I_D=-0.19A		1.5		nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.2		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-30V, V_{GS}=-10V, R_G=3Ω, I_D=-0.19A		2.3		ns
Turn-On Rise Time	t_r			16		
Turn-Off Delay Time	$t_{d(off)}$			11		
Turn-Off Fall Time	t_f			28		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

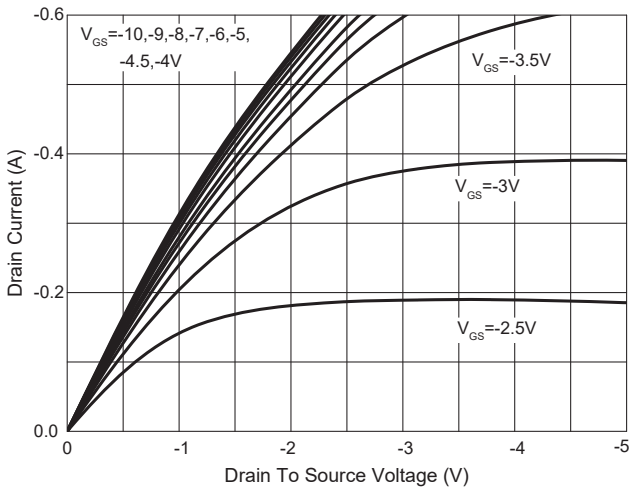


Fig. 2 - Transfer Characteristics

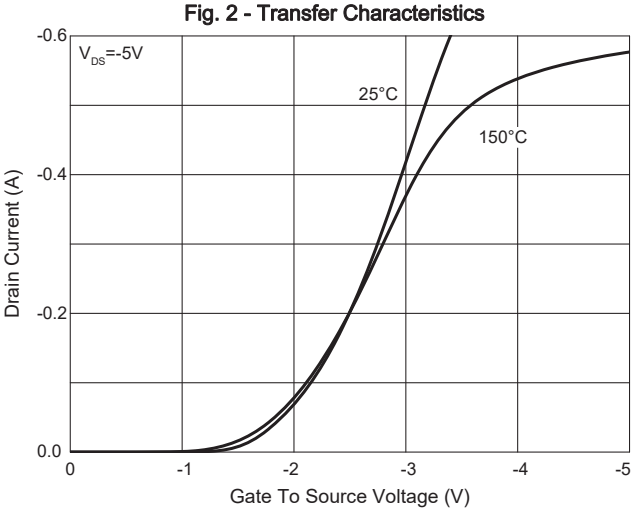


Fig.3 - $R_{DS(ON)}$ - V_{GS}

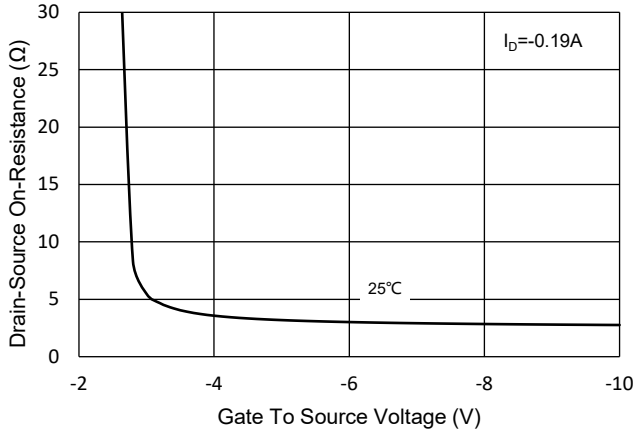


Fig.4 - $R_{DS(ON)}$ - I_D

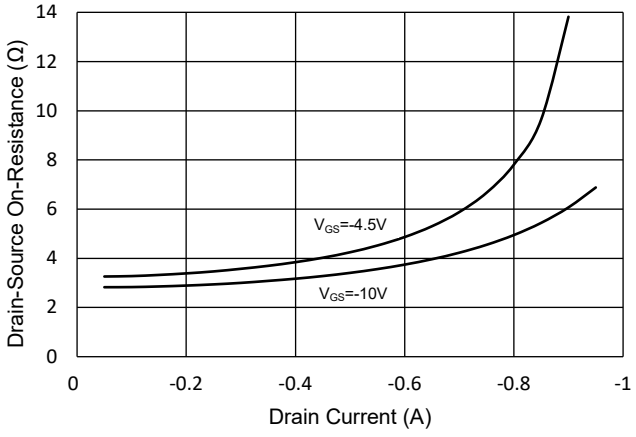


Fig. 5 - Capacitance Characteristics

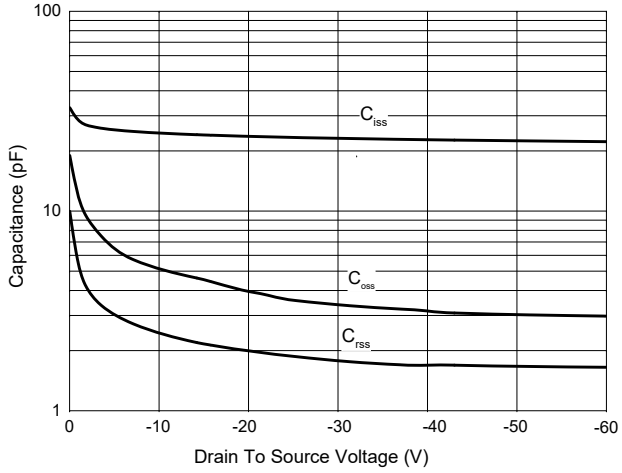
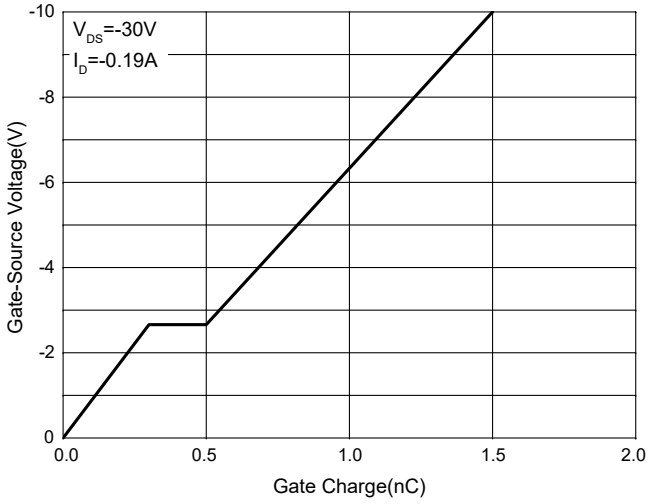


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - Normalized Threshold Voltage

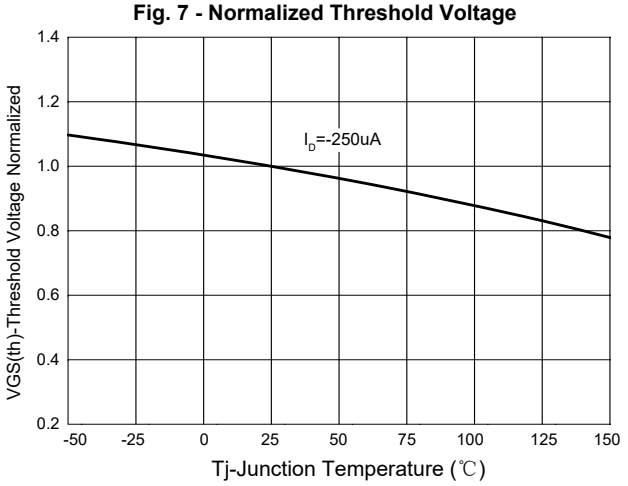


Fig.8 - Normalized On Resistance Characteristics

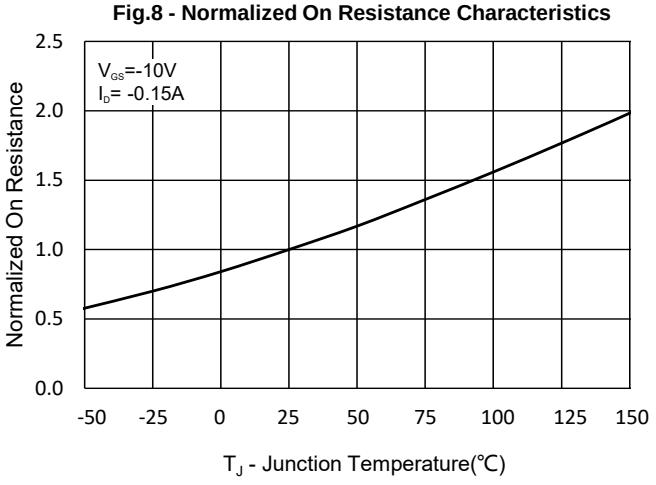


Fig.9 - I_S—V_{SD}

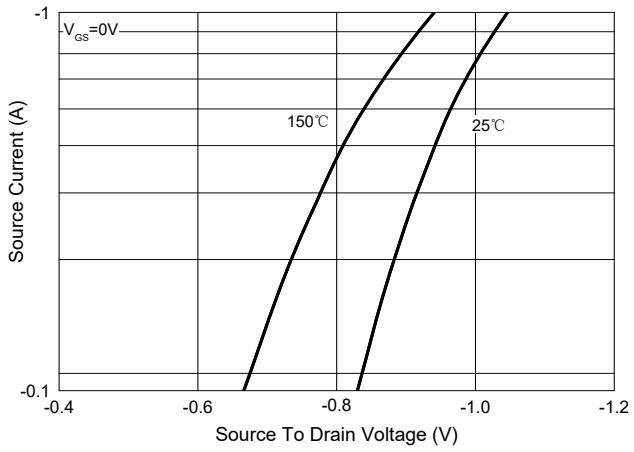


Fig. 10 - Drain Current

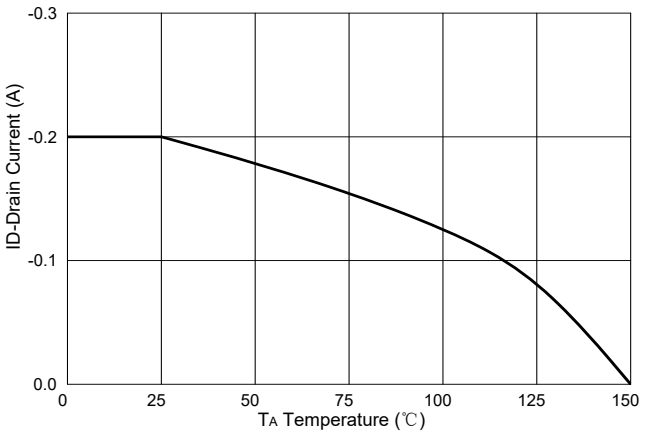
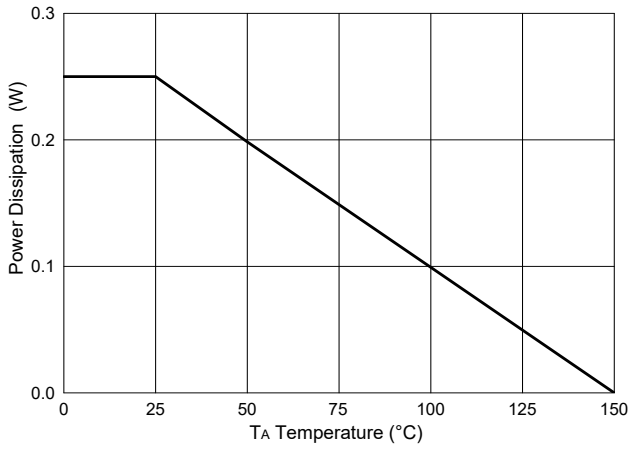


Fig.11-PD Dissipation



Curve Characteristics

Fig. 12 - Safe Operation Area

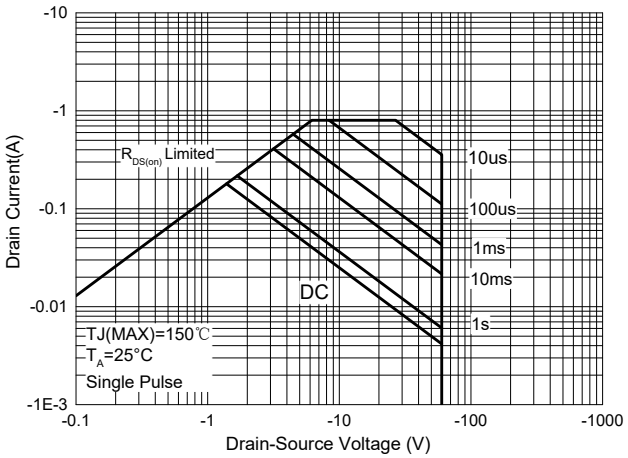
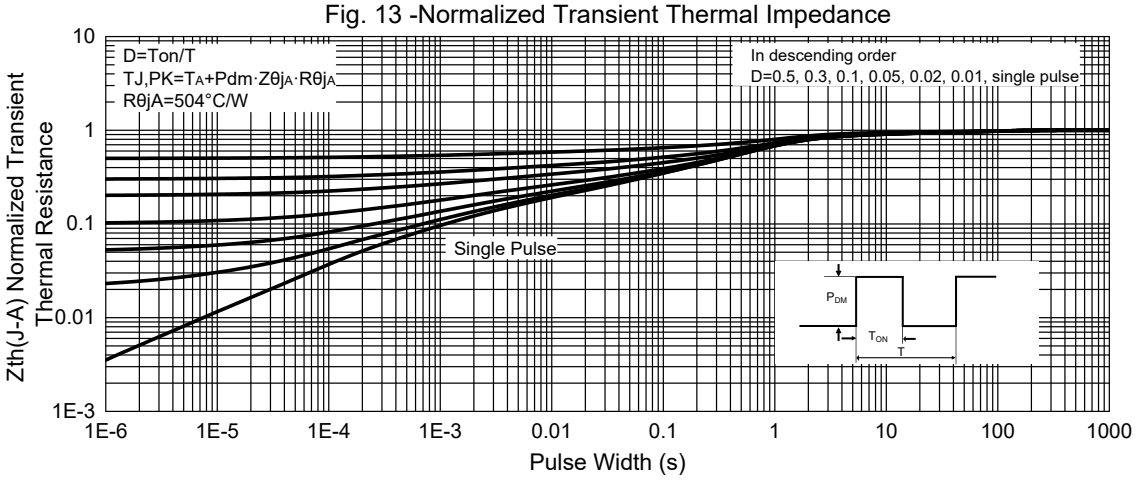


Fig. 13 -Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel